

PMEM1505PG

PNP transistor/Schottky rectifier module

Rev. 01 — 26 May 2004

Product data sheet

1. Product profile

1.1 General description

Combination of an PNP transistor with low V_{CEsat} and high current capability and a planar Schottky barrier rectifier with an integrated guard ring for stress protection in a SOT353 (SC-88A) small plastic package. NPN complement: PMEM1505NG.

1.2 Features

- 300 mW total power dissipation
- Current capability up to 0.5 A
- Reduces printed-circuit board area required
- Reduces pick and place costs
- Small plastic SMD package
- Transistor
 - ◆ Low collector-emitter saturation voltage.
- Diode
 - ◆ Ultra high-speed switching
 - ◆ Very low forward voltage
 - ◆ Guard ring protected.

1.3 Applications

- DC-to-DC converters
- Inductive load drivers
- General purpose load drivers
- Reverse polarity protection circuits
- MOSFET drivers.

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PNP transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	-15	V
I_C	collector current (DC)	continuous	[1]	-	-0.5	A
Schottky barrier rectifier						
V_R	continuous reverse voltage		-	-	20	V
I_F	continuous forward current		-	-	0.5	A

[1] Mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint for SOT353.

2. Pinning information

Table 2: Discrete pinning

Pin	Description	Simplified outline	Symbol
1	anode	<p>Top view</p>	<p>sym024</p>
5	cathode		
4	collector		
2	base		
3	emitter		

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PMEM1505PG	-	plastic surface mounted package; 5 leads	SOT353

4. Marking

Table 4: Marking

Type number	Marking code ^[1]
PMEM1505PG	L6*

- [1] * = p: made in Hong Kong.
 * = t: made in Malaysia.
 * = W: made in China.

5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
PNP transistor					
V_{CBO}	collector-base voltage	open emitter	-	-15	V
V_{CEO}	collector-emitter voltage	open base	-	-15	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I_C	collector current (DC)	continuous	^[1]	-0.5	A
		continuous	^[2]	-0.6	A
		continuous; $T_s \leq 55\text{ }^\circ\text{C}$	^[3]	-1	A
I_{CM}	peak collector current		-	-1	A
I_{BM}	peak base current		-	-100	mA

Table 5: Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
P_{tot}	total power dissipation	$T_{\text{amb}} \leq 25\text{ °C}$	[1]	-	200	mW
		$T_{\text{amb}} \leq 25\text{ °C}$	[2]	-	250	mW
		$T_{\text{s}} \leq 55\text{ °C}$	[3]	-	800	mW
T_{j}	junction temperature		-	150	°C	
Schottky barrier rectifier						
V_{R}	continuous reverse voltage		-	20	V	
I_{F}	continuous forward current		-	0.5	A	
I_{FSM}	non-repetitive peak forward current	$t = 8.3\text{ ms}$ square wave	-	5	A	
P_{tot}	total power dissipation	$T_{\text{amb}} \leq 25\text{ °C}$	[1]	-	200	mW
		$T_{\text{amb}} \leq 25\text{ °C}$	[2]	-	250	mW
		$T_{\text{s}} \leq 55\text{ °C}$	[3]	-	800	mW
T_{j}	junction temperature		[2]	-	125	°C
Combined device						
P_{tot}	total power dissipation	$T_{\text{amb}} \leq 25\text{ °C}$	[2]	-	300	mW
T_{stg}	storage temperature		-65	+150	°C	
T_{amb}	operating ambient temperature		[2]	-65	+150	°C

[1] Mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint for SOT353.

[2] Device mounted on a printed-circuit board, single-sided copper, tin-plated, 1 cm² mounting pad for both collector and cathode.

[3] Solder point of collector or cathode tab.

6. Thermal characteristics

Table 6: Thermal characteristics [1]

Symbol	Parameter	Conditions	Typ	Unit	
Single device					
$R_{\text{th(j-s)}}$	from junction to solder point	in free air	[2]	120	K/W
$R_{\text{th(j-a)}}$	from junction to ambient	in free air	[3]	395	K/W
			[4]	495	K/W
Combined device					
$R_{\text{th(j-a)}}$	from junction to ambient	in free air	[5]	410	K/W

[1] For Schottky barrier rectifiers thermal run-away has to be considered, as in some applications the reverse power losses P_{R} are a significant part of the total power losses. Nomograms for determining the reverse power losses P_{R} and $I_{\text{F(AV)}}$ rating will be available on request.

[2] Solder point of collector or cathode tab.

[3] Device mounted on a printed-circuit board, single-sided copper, tin-plated, 1 cm² mounting pad for both collector and cathode.

[4] Mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint for SOT353.

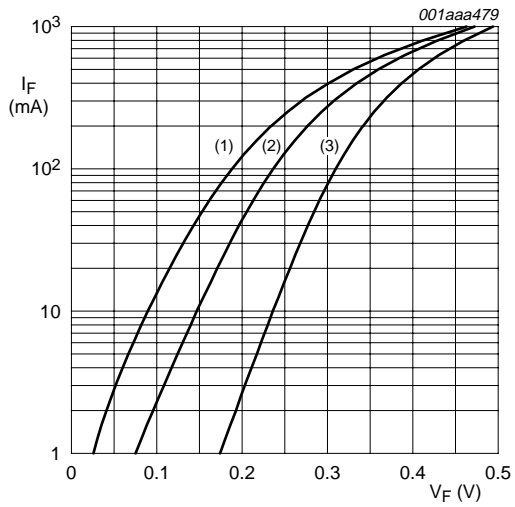
[5] Mounted on a ceramic printed-circuit board, single-sided copper, tin-plated, standard footprint.

7. Characteristics

Table 7: Characteristics
 $T_{amb} = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
PNP transistor							
I_{CBO}	collector-base cut-off current	$V_{CB} = -15\text{ V}; I_E = 0\text{ A}$	-	-	-100	nA	
		$V_{CB} = -15\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$	-	-	-50	μA	
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-100	nA	
h_{FE}	DC current gain	$V_{CE} = -2\text{ V}; I_C = -10\text{ mA}$	200	-	-		
		$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}$	150	-	-		
		$V_{CE} = -2\text{ V}; I_C = -500\text{ mA}$	90	-	-		
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	[1]	-	-25	mV	
		$I_C = -200\text{ mA}; I_B = -10\text{ mA}$	-	-	-150	mV	
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	-	-	-250	mV	
R_{CEsat}	equivalent on-resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	[1]	-	300	$< 500\text{ m}\Omega$	
V_{BEsat}	base-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	[1]	-	-1.1	V	
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}$	[1]	-	-0.9	V	
f_T	transition frequency	$V_{CE} = -10\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	[1]	100	280	MHz	
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	-	4.4	10	pF	
Schottky barrier rectifier							
V_F	continuous forward voltage	see Figure 1					
		$I_F = 10\text{ mA}$	[1]	-	240	270	mV
		$I_F = 100\text{ mA}$	[1]	-	300	350	mV
		$I_F = 500\text{ mA}$	[1]	-	400	460	mV
I_R	reverse current	see Figure 2					
		$V_R = 5\text{ V}$	[1]	-	5	10	μA
		$V_R = 8\text{ V}$	[1]	-	7	20	μA
		$V_R = 15\text{ V}$	[1]	-	10	50	μA
C_d	diode capacitance	$V_R = 5\text{ V}; f = 1\text{ MHz};$ see Figure 3	-	19	25	pF	

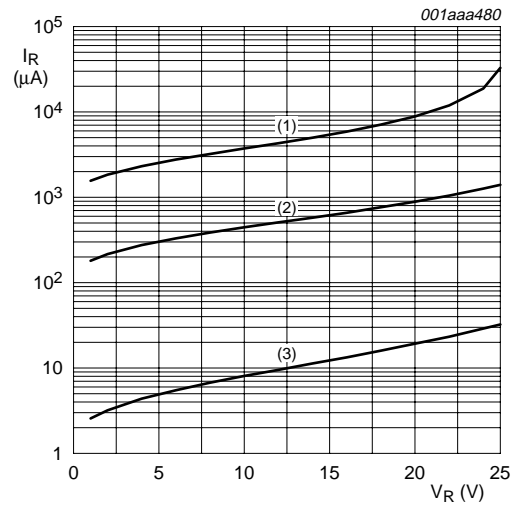
[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.



Schottky barrier rectifier.

- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

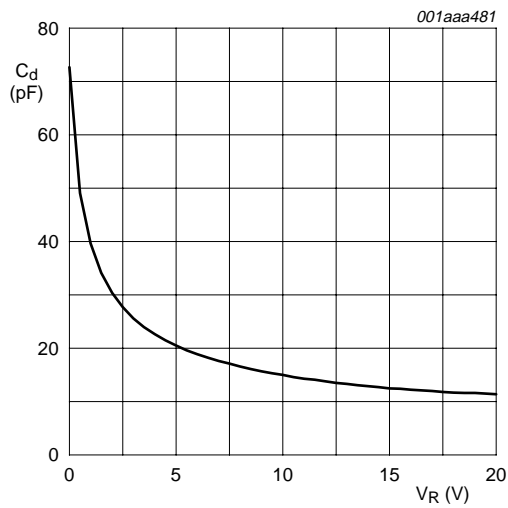
Fig 1. Forward current as a function of forward voltage; typical values.



Schottky barrier rectifier.

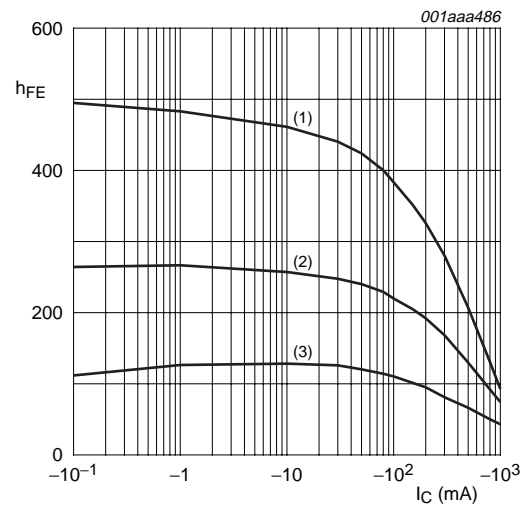
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig 2. Reverse current as a function of reverse voltage; typical values.



Schottky barrier rectifier; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

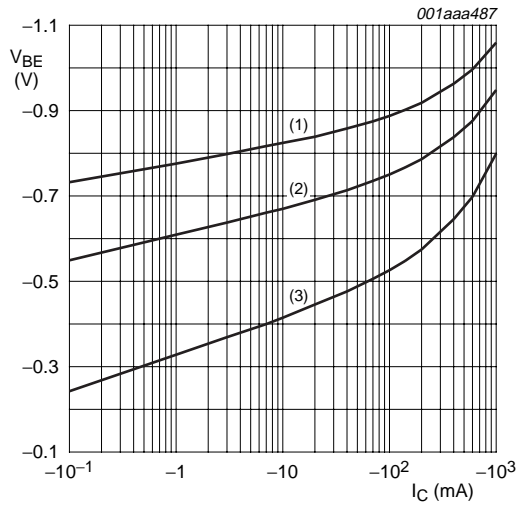
Fig 3. Diode capacitance as a function of reverse voltage; typical values.



PNP transistor; $V_{CE} = -2\text{ V}$.

- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$.

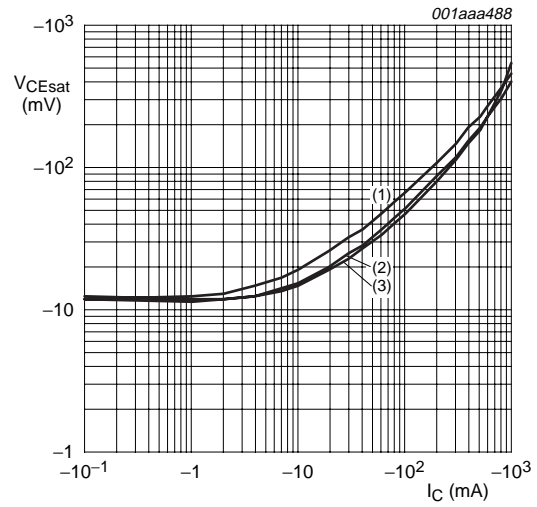
Fig 4. DC current gain as a function of collector current; typical values.



PNP transistor; $V_{CE} = -2\text{ V}$.

- (1) $T_{amb} = -55\text{ °C}$.
- (2) $T_{amb} = 25\text{ °C}$.
- (3) $T_{amb} = 150\text{ °C}$.

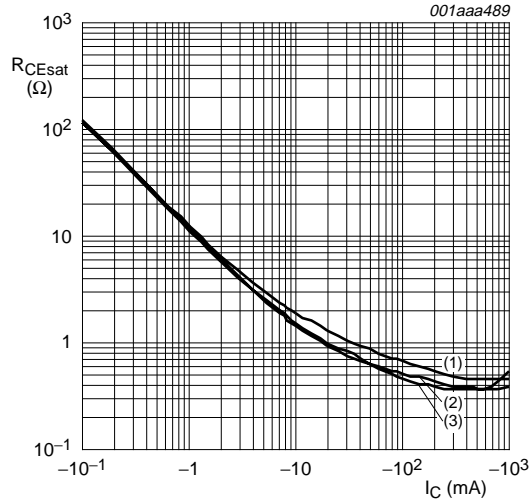
Fig 5. Base-emitter voltage as a function of collector current; typical values.



PNP transistor; $I_C/I_B = 20$.

- (1) $T_{amb} = 150\text{ °C}$.
- (2) $T_{amb} = 25\text{ °C}$.
- (3) $T_{amb} = -55\text{ °C}$.

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values.

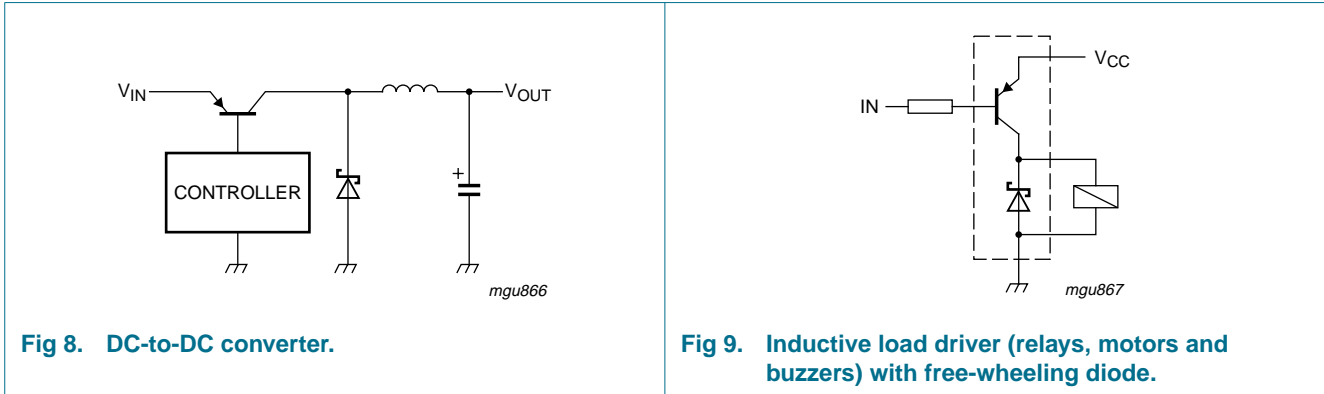


PNP transistor; $V_{CE} = -2\text{ V}$.

- (1) $T_{amb} = 150\text{ °C}$.
- (2) $T_{amb} = 25\text{ °C}$.
- (3) $T_{amb} = -55\text{ °C}$.

Fig 7. Equivalent on-resistance as a function of collector current; typical values.

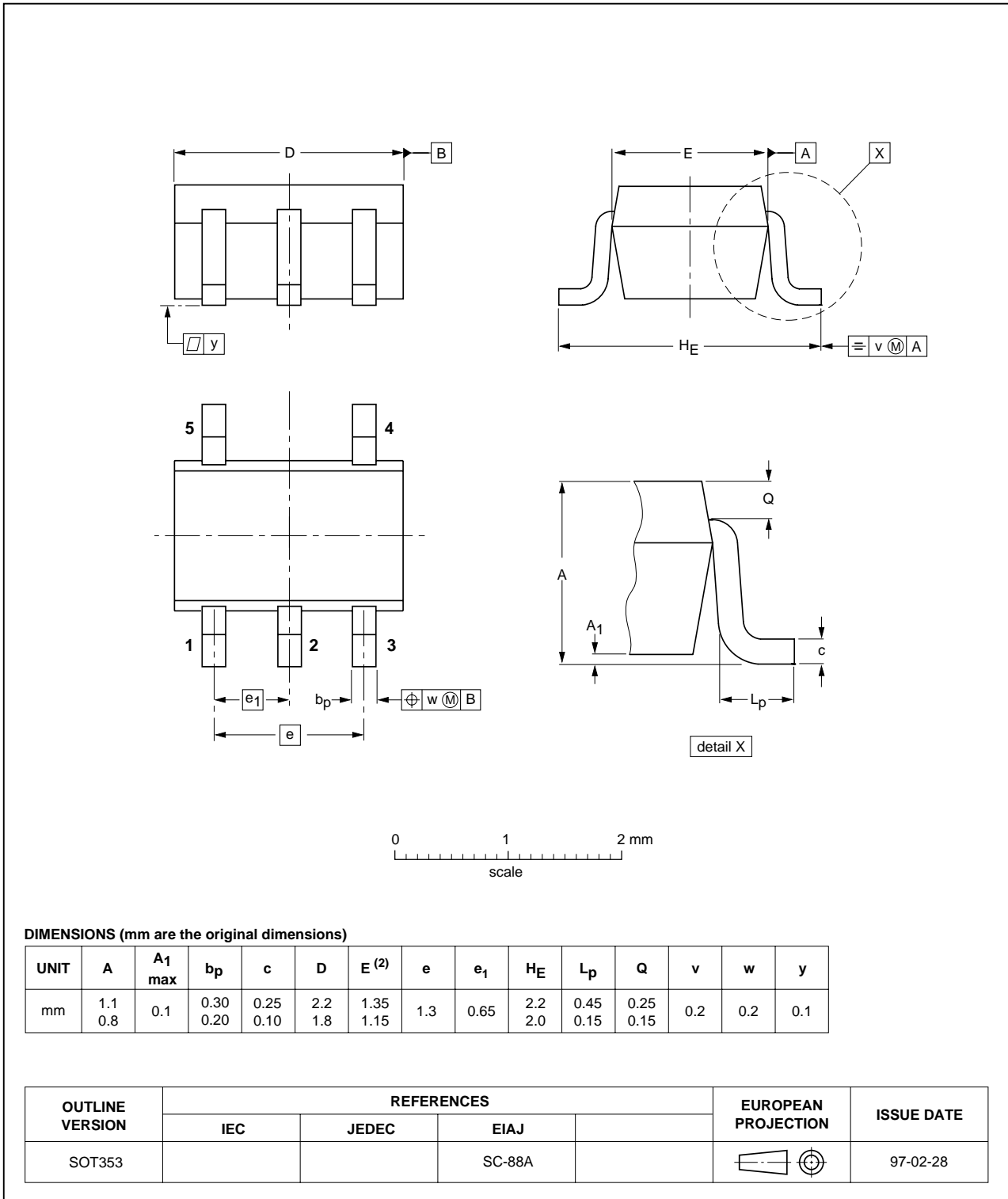
8. Application information



9. Package outline

Plastic surface mounted package; 5 leads

SOT353



www.DataSheet4U.com
Fig 10. Package outline.

10. Revision history

Table 8: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
PMEM1505PG_1	20040526	Product data	-	9397 750 12751	-

11. Data sheet status

Level	Data sheet status ^[1]	Product status ^[2] ^[3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

12. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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